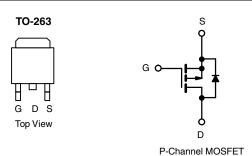


www.vishay.com

Vishay Siliconix

# Automotive P-Channel 30 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	- 30			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.0070			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.0110			
I <sub>D</sub> (A)	- 50			
Configuration	Single			



#### **FEATURES**

- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- 100 % R<sub>q</sub> and UIS Tested
- AEC-Q101 Qualified<sup>d</sup>
- Material categorization:
   For definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>



FREE

ORDERING INFORMATION	
Package	TO-263
Lead (Pb)-free and Halogen-free	SQM50P03-07-GE3

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		$V_{DS}$	- 30	V	
Gate-Source Voltage	$V_{GS}$	± 20	V		
Continuous Drain Currenta	T <sub>C</sub> = 25 °C	,	- 50		
Continuous Drain Current	T <sub>C</sub> = 125 °C	- I <sub>D</sub>	- 50		
Continuous Source Current (Diode Conduc	I <sub>S</sub>	- 50	Α		
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	- 200			
Single Pulse Avalanche Current		I <sub>AS</sub>	- 50		
Single Pulse Avalanche Energy	L = 0.1 mH	E <sub>AS</sub>	125	mJ	
M	T <sub>C</sub> = 25 °C	D	150	14/	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 125 °C	$P_{D}$	50	W	
Operating Junction and Storage Temperatu	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C		

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient	PCB Mount <sup>c</sup>	$R_{thJA}$	40	°C/W		
Junction-to-Case (Drain)		$R_{thJC}$	1	C/VV		

### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



# Vishay Siliconix

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static		-						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		- 30	-	-	V	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	V <sub>GS</sub> , I <sub>D</sub> = - 250 μA	- 1.5	- 2.0	- 2.5	V	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 30 V	-	-	- 1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 30 V, T <sub>J</sub> = 125 °C	-	-	- 50	μΑ	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 30 V, T <sub>J</sub> = 175 °C	-	-	- 250	1	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = - 10 V	$V_{DS} \le -5 V$	- 120	-	-	Α	
		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 30 A	-	0.0050	0.0070	)	
Dunin Course On Otata Basistanas		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 30 A, T <sub>J</sub> = 125 °C	-	-	0.0102	Ω	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 30 A, T <sub>J</sub> = 175 °C	-	-	0.0118		
		V <sub>GS</sub> = - 4.5 V	I <sub>D</sub> = - 20 A	-	0.0089	0.0110		
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 30 A		-	62	=-	S	
Dynamic <sup>b</sup>		<u> </u>						
Input Capacitance	C <sub>iss</sub>			-	4304	5380	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = - 25 V, f = 1 MHz	-	764	955		
Reverse Transfer Capacitance	C <sub>rss</sub>	7		-	680	850		
Total Gate Charge <sup>c</sup>	Qg			-	103.5	155	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = - 10 V	$V_{DS} = -15 \text{ V}, I_{D} = -75 \text{ A}$	-	14.3	=-		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	26.9	=-		
Gate Resistance	R <sub>g</sub>		f = 1 MHz		2.85	4.3	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	11	17		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = -15 \text{ V}, R_L = 0.2 \Omega$ $I_D \cong -75 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 1 \Omega$		-	10	15	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	63	95		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	26	39		
Source-Drain Diode Ratings and Char	acteristics <sup>b</sup>	•			•			
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	- 200	Α	
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> =	- 45 A, V <sub>GS</sub> = 0 V	-	- 0.9	- 1.5	V	

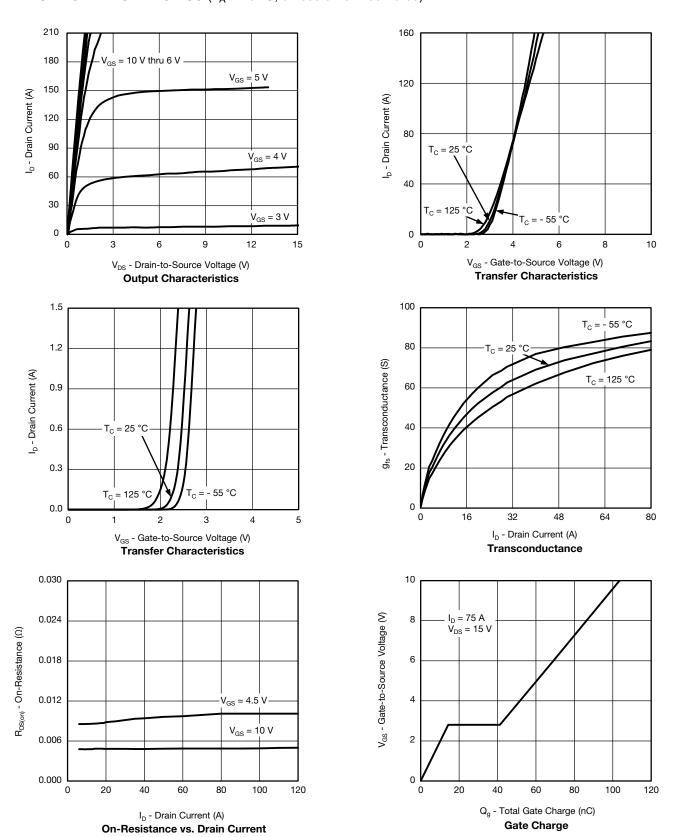
#### **Notes**

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

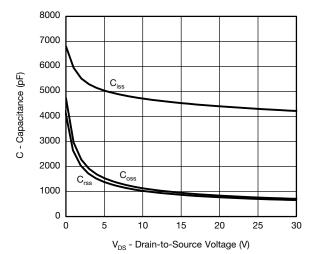


### TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)

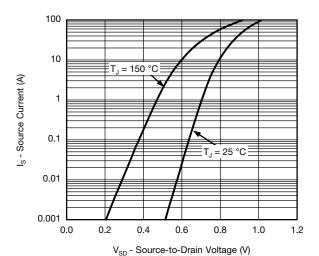




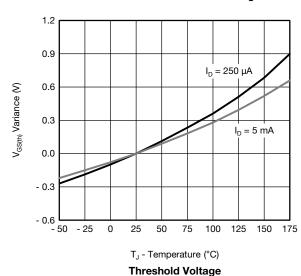
# **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

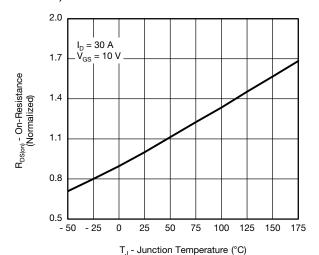


#### Capacitance

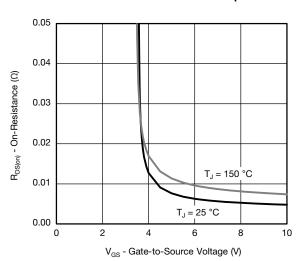


#### Source Drain Diode Forward Voltage

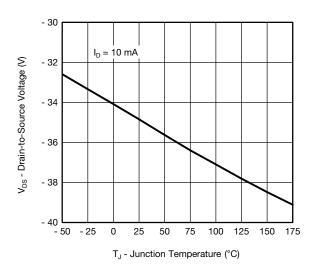




On-Resistance vs. Junction Temperature

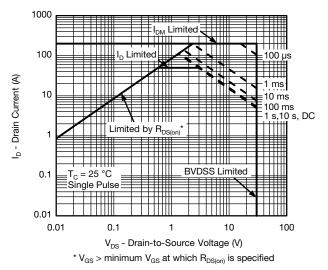


On-Resistance vs. Gate-to-Source Voltage

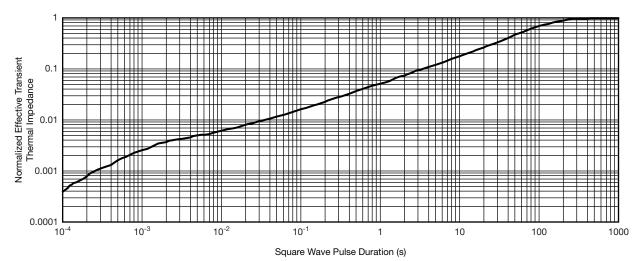


Drain Source Breakdown vs. Junction Temperature

### **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



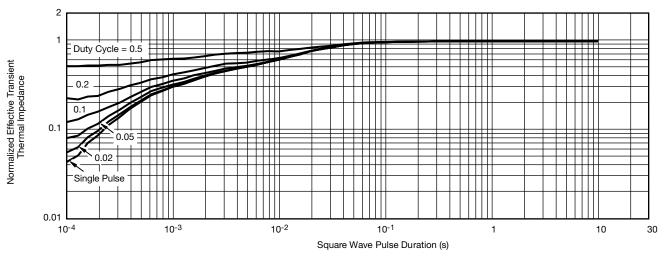
#### **Safe Operating Area**



Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix

### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

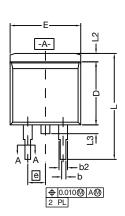
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

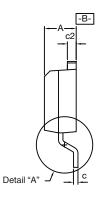
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?67044">www.vishay.com/ppg?67044</a>.

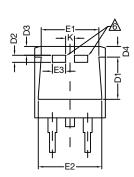




# TO-263 (D<sup>2</sup>PAK): 3-LEAD

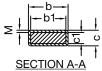








DETAIL A (ROTATED 90°)



1			1
≥⊹	<i>7777777</i>	붓	
ı	WHITTEN S	1	1

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. \*: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6 This feature is for thick lead.

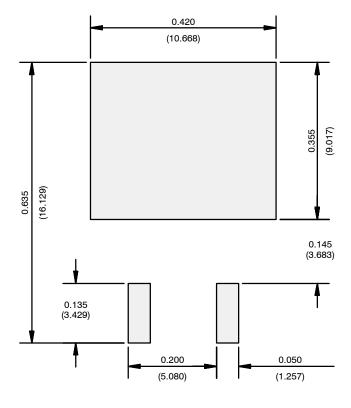
		INCHES		MILLIMETERS		
	DIM.	MIN.	MAX.	MIN.	MAX.	
Α		0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457	
	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
	D3	0.045	0.055	1.143	1.397	
	D4	0.044	0.052	1.118	1.321	
	Е	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	-	
	E2	0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
	е	0.100	BSC	2.54 BSC		
K		0.045	0.055	1.143	1.397	
L		0.575	0.625	14.605	15.875	
L1		0.090	0.110	2.286	2.794	
L2 L3		0.040	0.055	1.016	1.397	
		0.050	0.070	1.270	1.778	
L4		0.010 BSC		0.254 BSC		
	М	-	0.002	-	0.050	
ECI	ECN: T13-0707-Rev. K, 30-Sep-13					

DWG: 5843





### RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



Vishay

## **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

# 单击下面可查看定价,库存,交付和生命周期等信息

>>Vishay(威世)